

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In the Patent Application of  
Divisional of 09/048,288

Takashi NOGUCHI et al.

Examiner: Jack S. J. Chen

Application No.: Not yet assigned

Art Unit: 2813

Filed: January 8, 2004

For: METHOD OF FORMING N-AND P-CHANNEL  
FIELD EFFECT TRANSISTORS ON THE SAME  
SILICON LAYER HAVING A STREAM EFFECT

**PRELIMINARY AMENDMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Prior to the initial examination of the above-identified patent application, which is a Divisional of U.S. Patent Application No. 09/048,288, filed March 26, 1998, please amend the application as follows:

**Amendments to the Specification** begin on page 2 of this paper.

**Amendments to the Abstract** begin on page 4 of this paper

**Amendments to the Claims** are reflected in the listing of claims which begins on page 4 of this paper.

**Remarks/Arguments** begin on page 6 of this paper.